

TENTATIVE

CM100DUS-12F

Pre.	N.Honda	Rev	A	<i>S. Uchida</i>
Apr.	M.Tabata 28-Jan-'99			<i>M.Yamamoto May 16 '02</i>

HIGH POWER SWITCHING USE

Notice : This is not a final specification. Some parametric limits are subject to change.

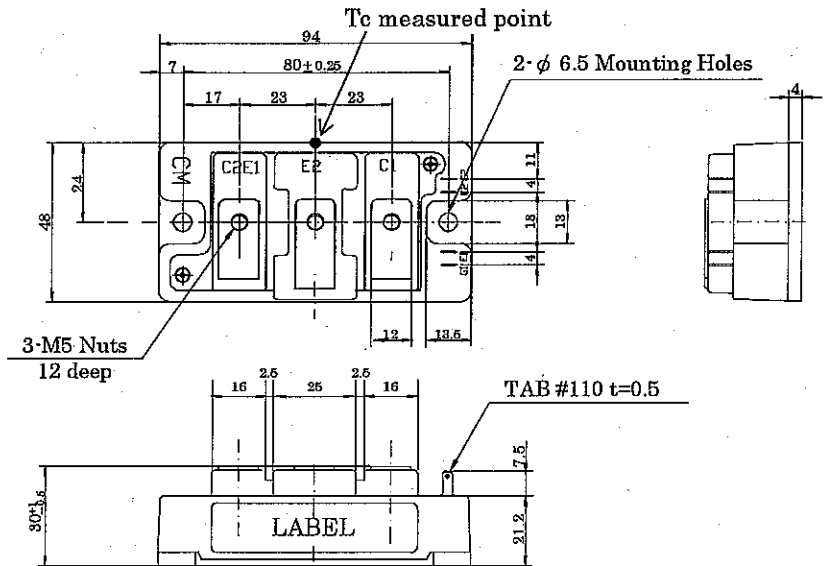
CM100DUS-12F

- I_C 100A
- V_{CES} 600V
- Insulated Type
- 2-elements in a pack

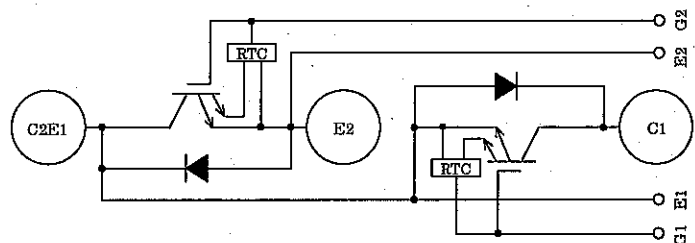
APPLICATION
Welder

OUTLINE DRAWING

Dimensions in mm



CIRCUIT DIAGRAM

ABSOLUTE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$)

Symbol	Item	Conditions	Ratings	Units
V_{CES}	Collector-emitter voltage	G-E Short	600	V
V_{GES}	Gate-emitter voltage	C-E Short	± 20	V
I_C	Collector current	$T_c = 25^\circ\text{C}$	100	A
I_{CM}		Pulse (2)	200	
I_E (1)	Emitter current	$T_c = 25^\circ\text{C}$	100	A
I_{EM} (1)		Pulse (2)	200	
P_c (3)	Maximum collector dissipation	$T_c = 25^\circ\text{C}$	350	W
T_J	Junction temperature		$-40 \sim +150$	$^\circ\text{C}$
T_{stg}	Storage temperature		$-40 \sim +125$	$^\circ\text{C}$
Viso	Isolation voltage	Charged part to base plate, AC 1 min.	2500	V
-	Torque strength	Main Terminals M 5	2.5 ~ 3.5	N·m
-		Mounting holes M 6	3.5 ~ 4.5	N·m
-	Weight	Typical value	310	g

ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$)

Symbol	Item	Conditions	Min.	Typ.	Max.	Units
I_{CES}	Collector cutoff current	$V_{CE}=V_{CES}, V_{GE}=0V$	-	-	1	mA
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=10mA, V_{CE}=10V$	5	6	7	V
I_{GES}	Gate leakage current	$V_{GE}=V_{CES}, V_{CE}=0V$	-	-	20	μA
$V_{CE(sat)}$	Collector to emitter saturation voltage	$T_j=25^\circ\text{C}$ $I_C=100A$ $T_j=125^\circ\text{C}$ $V_{GE}=15V$	1.7 -	2.0 1.95	2.7 -	V
C_{ies}	Input capacitance	$V_{CE}=10V$	-	-	27	nF
C_{oes}	Output capacitance	$V_{GE}=0V$	-	-	1.8	
C_{res}	Reverse transfer capacitance		-	-	1	
Q_G	Total gate charge	$V_{CC}=300V, I_C=100A$ $V_{GE}=15V$	-	620	-	nC
$t_{d(on)}$	Turn-on delay time	$V_{CC}=300V, I_C=100A$	-	-	100	ns
t_r	Turn-on rise time	$V_{GE1}=V_{GE2}=15V$	-	-	80	
$t_{d(off)}$	Turn-off delay time	$R_G=6.3\Omega$, Inductive load	-	-	300	
t_f	Turn-off fall time	switching operation	-	-	150	
t_{rr} ①	Reverse recovery time	$I_E=100A$	-	-	150	ns
Q_{rr} ①	Reverse recovery charge		-	1.9	-	μC
V_{EC} ①	Emitter-collector volatge	$I_E=100A, V_{GE}=0V$	-	-	2.6	V
$R_{th(j-c)Q}$	Thermal resistance*1	IGBT part(1/2 module)	-	-	0.35	$^\circ\text{C/W}$
$R_{th(j-c)R}$		FWDi part(1/2 module)	-	-	0.70	
$R_{th(c-f)}$	Contact thermal resistance	Case to fin, Thermal compound applied*2(1/2 module)	-	0.07	-	
$R_{th(j-c')Q}$	Thermal resistance	T_c measured point is just under the chips	-	0.23*3	-	

① $I_E, V_{EC}, t_{rr}, Q_{rr}$ & di/dt represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).

② Pulse width and repetition rate should be such that the device junction temp. (T_j) dose not exceed T_{jmax} rating.

③ Junction temperature (T_j) should not increase beyond 150°C .

④ Pulse width and repetition rate should be such as to cause neglible temperature rise.

*1: T_c measured point is shown in page "1-2".

*2: Typical value is measured by using Shin-etsu Silicone "G-746".

*3: If you use this value, $R_{th(f-a)}$ should be measured just under the chips.